HUASHUO SEMICONDUCTOR

HSM8P10

P-Ch 100V Fast Switching MOSFETs

Description

The HSM8P10 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

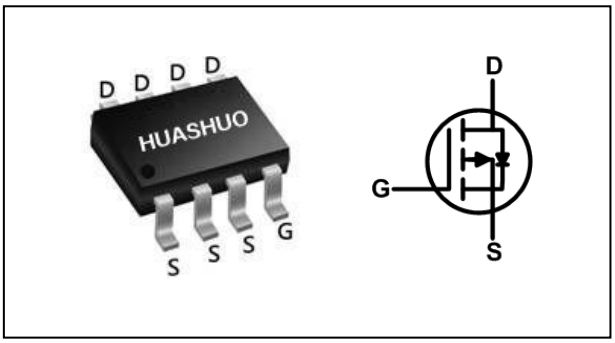
The HSM8P10 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	-100	V
$R_{DS(ON),max}$	110	mΩ
I_D	-8	A

SOP8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ -10V[1]	-8	A
I_D@T_C=70℃	Continuous Drain Current, V_{GS} @ -10V[1]	-3.8	A
I_{DM}	Pulsed Drain Current[2]	-18	A
EAS	Single Pulse Avalanche Energy[3]	55	mJ
I_{AS}	Avalanche Current	3.1	A
P_D@T_A=25℃	Total Power Dissipation[4]	3.1	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	61	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	17	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-100	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.03	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-6A	---	83	110	mΩ
		V_{GS}=-4.5V , I_D=-3A	---	95	120	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.2	-1.8	-2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.56	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-100V , V_{GS}=0V , T_J=25℃	---	---	50	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-10V , I_D=-3A	---	24	---	S
Q_g	Total Gate Charge	V_{DS}=-48V , V_{GS}=-10V , I_D=-3A	---	19.8	---	nC
Q_{gs}	Gate-Source Charge		---	3.9	---	
Q_{gd}	Gate-Drain Charge		---	4.5	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-50V , V_{GS}=-10V , R_G=3.3Ω, I_D=-1A	---	8.8	---	ns
T_r	Rise Time		---	29.6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	77.2	---	
T_f	Fall Time		---	89.6	---	
C_{iss}	Input Capacitance	V_{DS}=-20V , V_{GS}=0V , f=1MHz	---	1080	---	pF
C_{oss}	Output Capacitance		---	113	---	
C_{rss}	Reverse Transfer Capacitance		---	25	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	-8	A
I_{SM}	Pulsed Source Current[2,5]		---	---	-18	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1.2	V

Note :

1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3.The EAS data shows Max. rating . The test condition is V_{DD}=-80V,V_{GS}=-10V,L=0.1mH

4.The power dissipation is limited by 150℃ junction temperature

5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

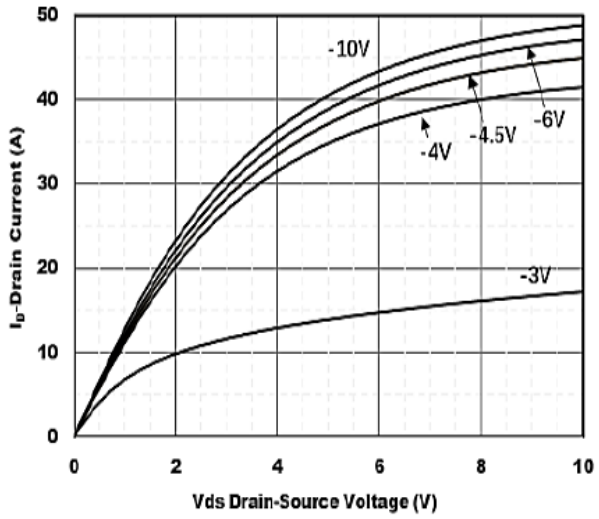


Figure1. Output Characteristics

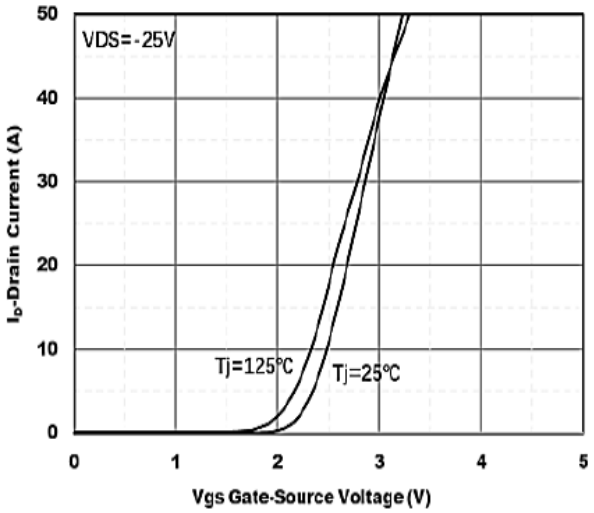


Figure2. Transfer Characteristics

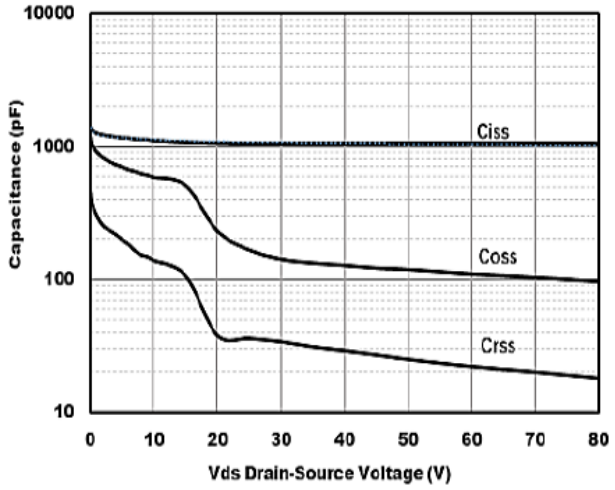


Figure3. Capacitance Characteristics

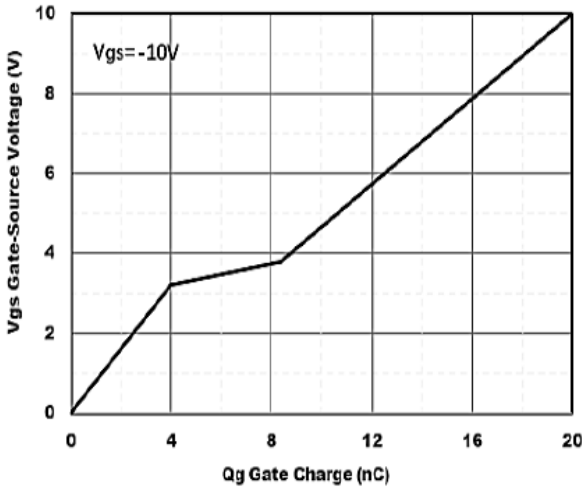


Figure4. Gate Charge

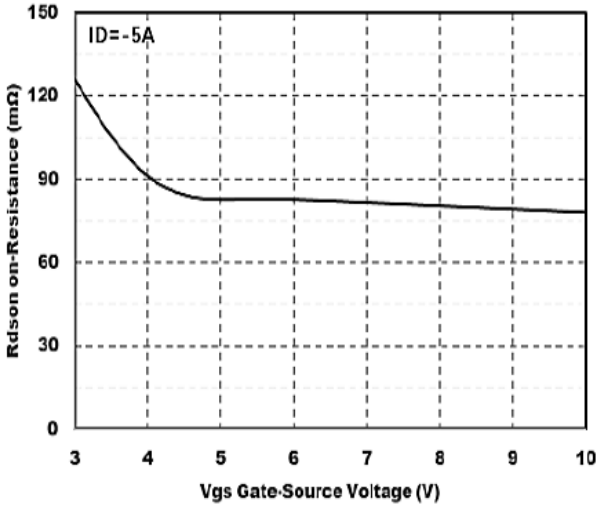


Figure5. : On-Resistance vs. Gate to Source Voltage

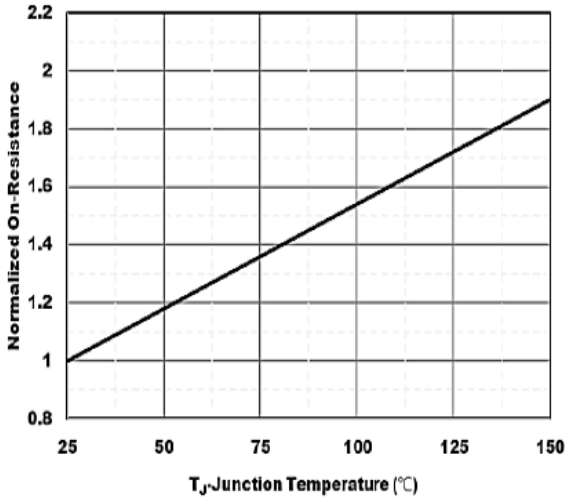


Figure6.Normalized On-Resistance

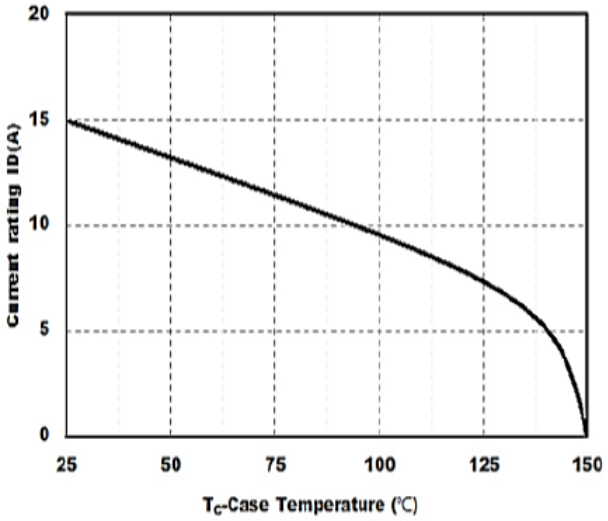


Figure7. Drain current

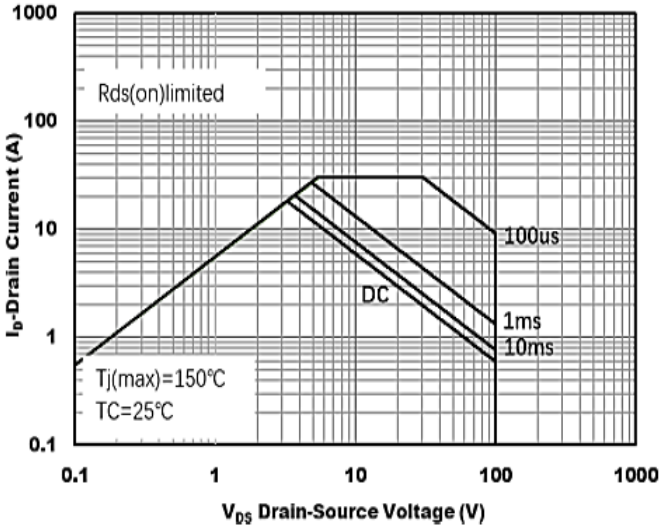


Figure8.Safe Operation Area

Figure9.Normalized Maximum Transient thermal impedance

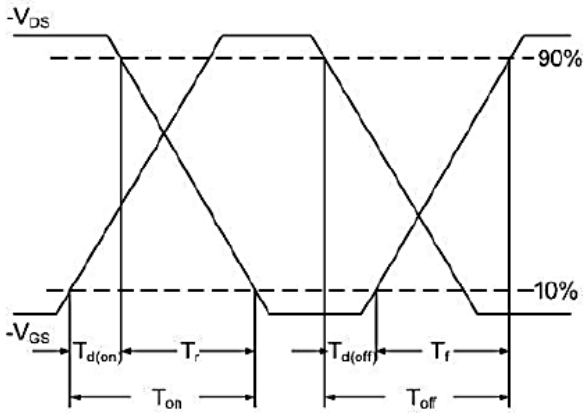


Figure10 Switching Time Waveform

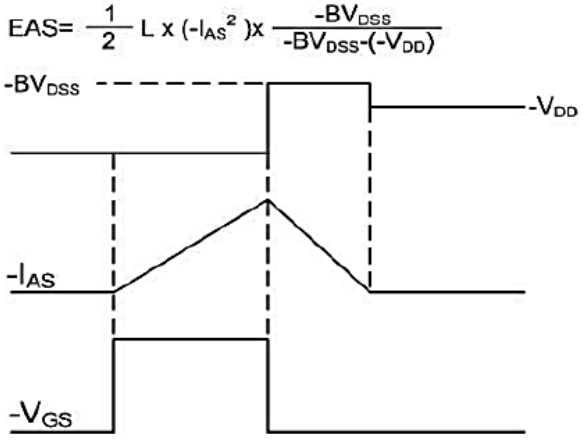
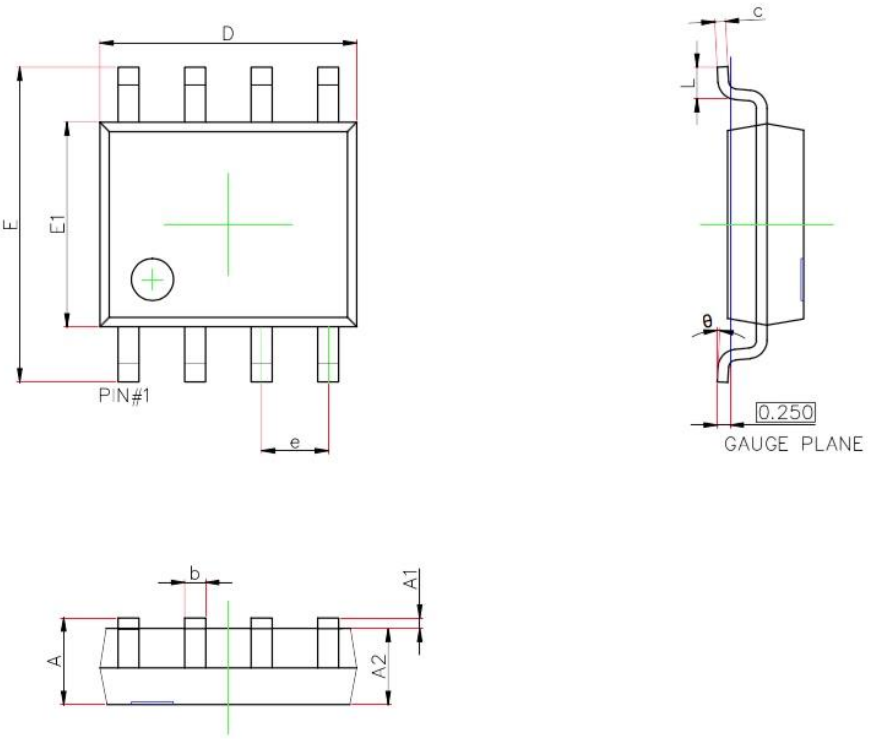


Figure11 Unclamped Inductive Waveform

Ordering Information

Part Number	Package code	Packaging
HSM8P10	SOP-8	3000/Tape&Reel

SOP8PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 （BSC）		0.050 （BSC）	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°